

ABSTRACT

10 Apparatus for the processing of materials involving
placing a material either placed between an radio-frequency
electrode and a ground electrode, or which is itself one of
the electrodes. This is done in atmospheric pressure
conditions. The apparatus effectively etches or cleans
15 substrates, such as silicon wafers, or provides cleaning of
spools and drums, and uses a gas containing an inert gas and
a chemically reactive gas.

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